

2SK3018W

30V N-Channel Enhancement Mode MOSFET

1. Description

This 30V N-channel MOSFET is based on MDD's unique device design to achieve low $R_{DS(on)}$, fast switching and good ESD rating performance.

2. Features

- Low on-resistance
- Fast switching speed
- Low voltage drive makes this device ideal for Portable equipment
- Easily designed drive circuits
- Easy to parallel
- Interfacing , Switching

3. Application

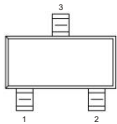
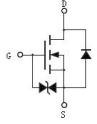
- Notebook
- Battery Protection
- Load Switch

4. Absolute Maximum Ratings($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	0.1	A
Power Dissipation	P_D	200	mW
Thermal Resistance From Junction to Ambient	$R_{\theta JA}$	625	$^{\circ}\text{C/W}$
Storage Temperature	T_{stg}	-55~+150	$^{\circ}\text{C}$
Junction Temperature	T_J	150	$^{\circ}\text{C}$

- Stresses exceeding Maximum Ratings may damage the device.
- Maximum Ratings are stress ratings only.
- Functional operation above the Recommended Operating Conditions is not implied.
- Extended exposure to stresses above the recommended Operating Conditions may affect device reliability

5. Pinning information

Pin	Symbol	Description	Simplified outline	Equivalent Circuit	Marking	Package
1	G	Gate			KN	SOT-323
2	S	Source				
3	D	Drain				

6. $T_A=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Condition	Min	Typ	Max	Unit
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=10\mu A$	30	—	—	V
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=3V, I_D=100\mu A$	0.8	1	1.5	V
I_{GSS}	Gate-body Leakage	$V_{DS}=0V, V_{GS}=\pm 20V$	—	—	± 3	μA
I_{DSS}	Zero Gate Voltage Drain current	$V_{DS}=30V, V_{GS}=0V$	—	—	0.2	μA
$R_{DS(ON)}$	Drain-Source On-Resistance	$V_{GS}=4V, I_D=10mA$	—	5	8	Ω
		$V_{GS}=2.5V, I_C=1mA$	—	8	13	Ω
V_{SD}	Diode Forward voltage	$V_{GS}=0V, I_S=0.1A$	—	—	1.2	V
I_S	Maximum Body-Diode Continuous Current		—	—	0.1	A

7. Dynamic Electrical Characteristics(note4)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS}=0V$	—	13	—	pF
C_{oss}	Output Capacitance	$V_{DS}=5V$	—	9	—	pF
C_{rss}	Reverse Transfer Capacitance	$f=1.0MHz$	—	4	—	pF

8. Switching Characteristics(note4)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
$t_{d(on)}$	Turn on Delay Time	$V_{GS}=5V$ $V_{DD}=5V$ $I_D=10mA$ $R_{GEN}=5\Omega$	—	15	—	nS
t_r	Turn on Rise Time		—	35	—	nS
$t_{d(off)}$	Turn Off Delay Time		—	80	—	nS
t_f	Turn Off Fall Time		—	80	—	nS

Notes: 1.Repetitive Rating: Pulse width limited by maximum junction temperature

2.This test is performed with on heat sink at $T_A=25^{\circ}\text{C}$

3.Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$

4.These parameters have no way to verify

9. Electrical Characteristics Diagrams

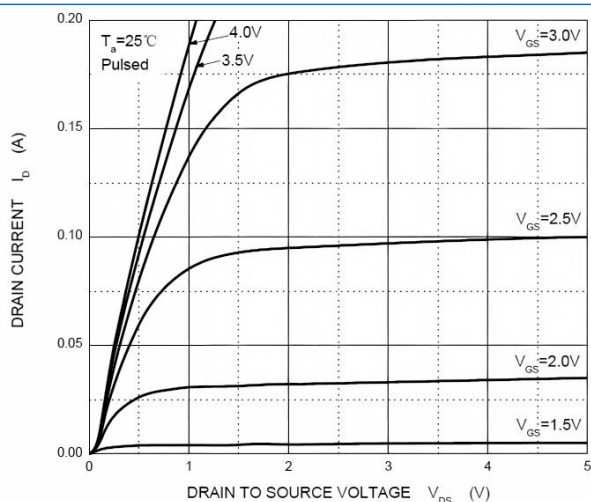


Figure 1. Output Characteristics

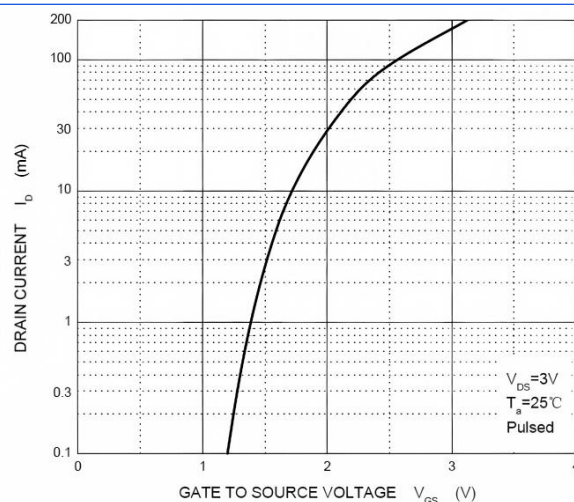


Figure 2. Transfer Characteristics

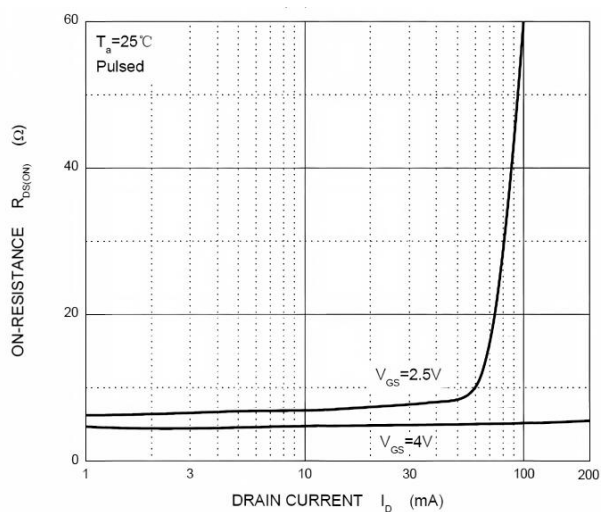


Figure 3. $R_{DS(on)}$ VS Drain Current

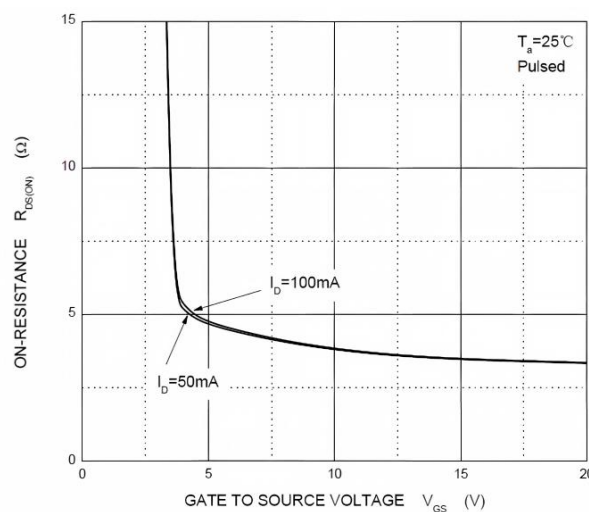


Figure 4. $R_{DS(on)}$ VS V_{GS}

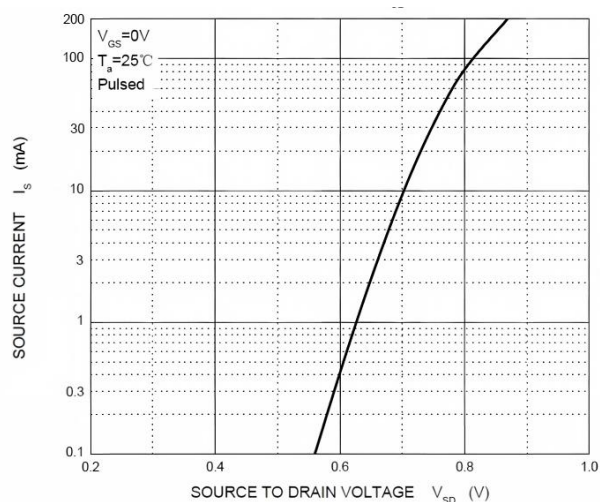
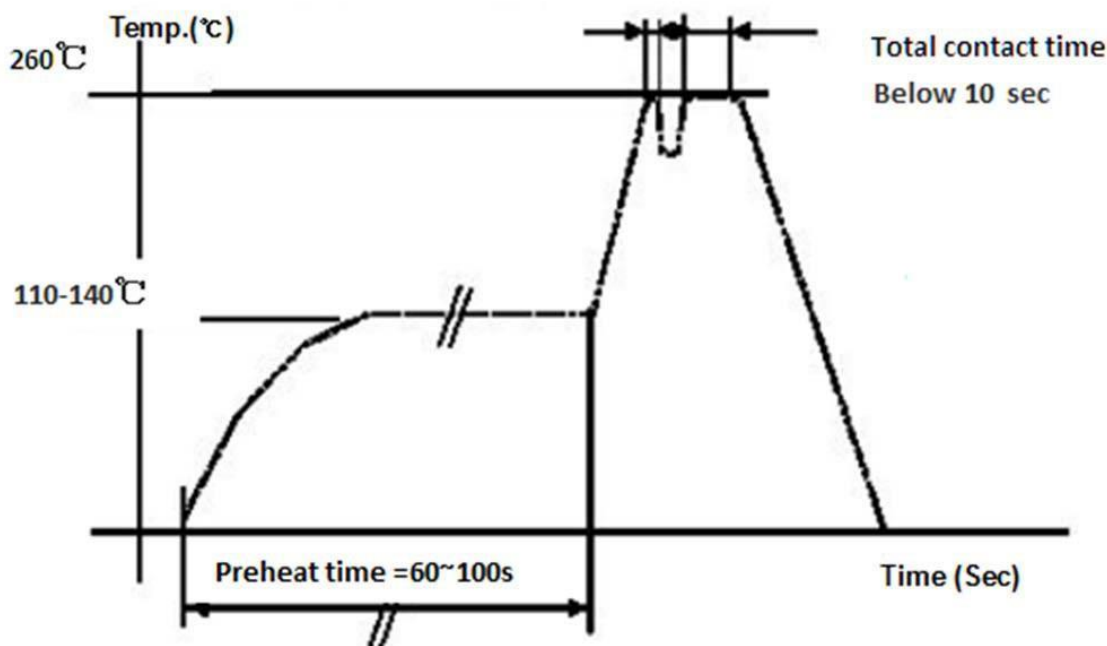


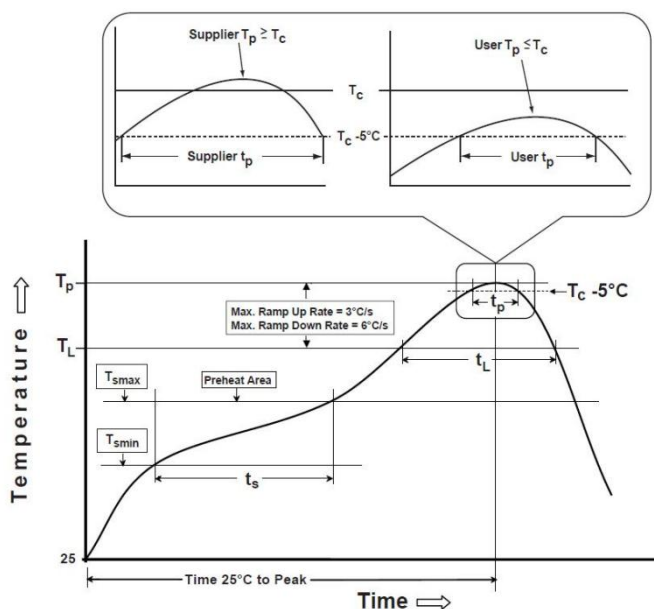
Figure 5. Source-Drain Diode Forward Characteristics

10.Recommended Soldering Profilefor Rectifier Diodes(PbFree)

a)Wave Soldering Profile



b)Reflow Soldering Profile(PbFreeApplication),refer to IPC/JEDEC J-STD-020

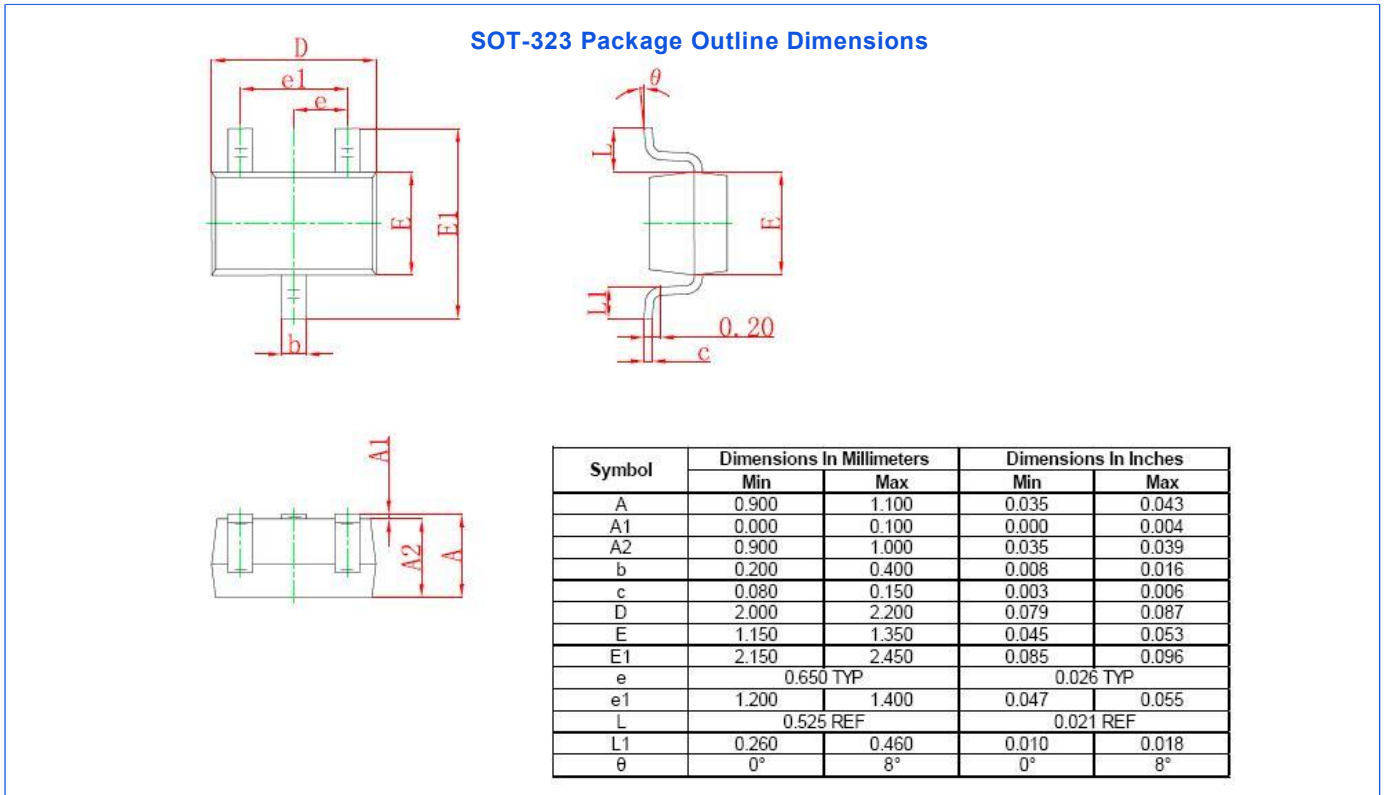


Preheat/Soak Temperature Min (T _{sm}) Temperature Max (T _{sm} max) Time (ts) from (T _{sm} to T _{sm} max)	50 °C 200 °C 60-120 seconds
Melting Point of Solder (Sn Ag Cu)	217°C
Ramp-up Rate to 217°C (Melting Point of Solder)	3°C/sec
Time at Temp. > 217°C (Melting Point of Solder)	60–150 Sec
Peak Temperature	255±5°C
Time within 5°C below Peak Temp.	20–40 Sec
Cooling Rate	6°C/sec (max)
Time from 25°C to Peak Temp.	8min (max)

c)Manual Soldering

When using an electric soldering iron for manual soldering, it is recommended that the temperature does not exceed 300°C and the soldering time is less than 10 seconds.

11. Outline Drawing



12. Important Notice and Disclaimer

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